

# Shunri Oda

## List of Publications by Citations

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51  
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357  
ext. papers

4,966  
ext. citations

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avg, IF

5.27  
L-index

#	Paper	IF	Citations
293	A quantum-dot spin qubit with coherence limited by charge noise and fidelity higher than 99.9. <i>Nature Nanotechnology</i> , <b>2018</b> , 13, 102-106	28.7	340
292	Photoluminescence mechanism in surface-oxidized silicon nanocrystals. <i>Physical Review B</i> , <b>1997</b> , 55, R7375-R7378	3.5	174
291	A fault-tolerant addressable spin qubit in a natural silicon quantum dot. <i>Science Advances</i> , <b>2016</b> , 2, e1600694	10.9	120
290	A flexible and wearable terahertz scanner. <i>Nature Photonics</i> , <b>2016</b> , 10, 809-813	33.9	106
289	Electron trapping, storing, and emission in nanocrystalline Si dots by capacitance-voltage and conductance-voltage measurements. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 576-581	2.5	101
288	Fabrication of Nanocrystalline Silicon with Small Spread of Particle Size by Pulsed Gas Plasma. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4031-4034	1.4	100
287	Nanocrystalline silicon electron emitter with a high efficiency enhanced by a planarization technique. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 2748-2757	2.5	89
286	Highly Oriented ZnO Films Prepared by MOCVD from Diethylzinc and Alcohols. <i>Japanese Journal of Applied Physics</i> , <b>1985</b> , 24, 1607-1610	1.4	78
285	Diagnostic Study of VHF Plasma and Deposition of Hydrogenated Amorphous Silicon Films. <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, 1889-1895	1.4	71
284	ZnS blue-light-emitting diodes with an external quantum efficiency of 510%. <i>Applied Physics Letters</i> , <b>1975</b> , 27, 697-699	3.4	71
283	Preparation of Polycrystalline Silicon by Hydrogen-Radical-Enhanced Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1987</b> , 26, L10-L13	1.4	70
282	Electron Transport in Nanocrystalline Si Based Single Electron Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 4647-4650	1.4	69
281	Charge injection and trapping in silicon nanocrystals. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 182101	3.4	60
280	Emission lifetime of polarizable charge stored in nano-crystalline Si based single-electron memory. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 6402-6408	2.5	57
279	Growth of Amorphous and Crystalline Silicon by HR-CVD (Hydrogen Radical Enhanced CVD). <i>Materials Research Society Symposia Proceedings</i> , <b>1987</b> , 95, 225		56
278	Quantum confinement energy in nanocrystalline silicon dots from high-frequency conductance measurement. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 7261-7265	2.5	54
277	A new emission band in self-activated ZnS. <i>Journal of Luminescence</i> , <b>1979</b> , 18-19, 829-832	3.8	45

276	Hopping conduction in size-controlled Si nanocrystals. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 014303	2.5	42
275	Frequency effects in processing plasmas of the VHF band. <i>Plasma Sources Science and Technology</i> , <b>1993</b> , 2, 26-29	3.5	42
274	Fabrication and Electrical Characteristics of Single Electron Tunneling Devices Based on Si Quantum Dots Prepared by Plasma Processing. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4038-4041	1.4	41
273	Preparation of Microcrystalline Silicon Films by Very-High-Frequency Digital Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, 1948-1952	1.4	41
272	Magnetic field dependence of Pauli spin blockade: A window into the sources of spin relaxation in silicon quantum dots. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	40
271	Study of structural and optical properties of nanocrystalline silicon embedded in SiO <sub>2</sub> . <i>Thin Solid Films</i> , <b>2000</b> , 375, 137-141	2.2	40
270	Selective Etching of Hydrogenated Amorphous Silicon by Hydrogen Plasma. <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, 4442-4445	1.4	39
269	Probing electron charging in nanocrystalline Si dots using Kelvin probe force microscopy. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 3262-3264	3.4	34
268	Evidence of storing and erasing of electrons in a nanocrystalline-Si based memory device at 77 K. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2002</b> , 20, 1135		34
267	The Role of Hydrogen Radicals in the Growth of a-Si and Related Alloys. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, L188-L190	1.4	34
266	Preparation of a-Si:H Films by VHF Plasma CVD. <i>Materials Research Society Symposia Proceedings</i> , <b>1988</b> , 118, 117		34
265	Nanocrystalline silicon formation in a SiH <sub>4</sub> plasma cell. <i>Journal of Non-Crystalline Solids</i> , <b>1996</b> , 198-200, 875-878	3.9	33
264	Charge storage in nitrided nanocrystalline silicon dots. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 173107	3.4	32
263	Electron transport in a single silicon quantum structure using a vertical silicon probe. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 4186	2.5	32
262	NeoSilicon materials and silicon nanodevices. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2003</b> , 101, 19-23	3.1	31
261	Enhanced Dielectric Properties in SrTiO <sub>3</sub> /BaTiO <sub>3</sub> Strained Superlattice Structures Prepared by Atomic-Layer Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 6817-6820	1.4	31
260	Tip-enhanced Raman mapping of a single Ge nanowire. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 053112	3.4	30
259	Nanoelectromechanical nonvolatile memory device incorporating nanocrystalline Si dots. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 094306	2.5	29

258	Toward long-term retention-time single-electron-memory devices based on nitrided nanocrystalline silicon dots. <i>IEEE Nanotechnology Magazine</i> , <b>2004</b> , 3, 210-214	2.6	29
257	Properties of a-Si based alloys prepared from fluorides and hydrogen. <i>Journal of Non-Crystalline Solids</i> , <b>1985</b> , 77-78, 877-880	3.9	29
256	Observation of the single electron charging effect in nanocrystalline silicon at room temperature using atomic force microscopy. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 1089-1091	3.4	27
255	Preparation of Nanocrystalline Silicon by Pulsed Plasma Processing. <i>Materials Research Society Symposia Proceedings</i> , <b>1994</b> , 358, 721		27
254	Epitaxial Growth of YBaCuO Films on Sapphire at 500°C by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, L427-L429	1.4	27
253	Properties of Metalorganic Precursors for Chemical Vapor Deposition of Oxide Superconductors. <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, L1072-L1074	1.4	27
252	Hydrogen radical assisted chemical vapor deposition of ZnSe. <i>Applied Physics Letters</i> , <b>1986</b> , 48, 33-35	3.4	27
251	Room temperature single electron charging in single silicon nanochains. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 053705	2.5	26
250	Thermal-aware device design of nanoscale bulk/SOI FinFETs: Suppression of operation temperature and its variability <b>2011</b> ,		25
249	Influence of nanocrystal size on the transport properties of Si nanocrystals. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 024518	2.5	25
248	Construction of amorphous silicon ISFET. <i>Sensors and Actuators</i> , <b>1989</b> , 16, 55-65		25
247	Utilizing self-assembled-monolayer-based gate dielectrics to fabricate molybdenum disulfide field-effect transistors. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 041605	3.4	24
246	Single-Electron Tunneling Devices Based on Silicon Quantum Dots Fabricated by Plasma Process. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 264-267	1.4	24
245	Carrier conduction in a Si-nanocrystal-based single-electron transistor-I. Effect of gate bias. <i>Superlattices and Microstructures</i> , <b>2000</b> , 28, 177-187	2.8	23
244	Single Electron Memory Devices Based on Plasma-Derived Silicon Nanocrystals. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, L855-L857	1.4	23
243	Visible Electroluminescence from Spherical-Shaped Silicon Nanocrystals. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 8137-8140	1.4	22
242	Preparation and characterization of low-resistivity ZnS for blue LED. <i>IEEE Transactions on Electron Devices</i> , <b>1977</b> , 24, 956-958	2.9	22
241	Characterization and suppression of low-frequency noise in Si/SiGe quantum point contacts and quantum dots. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 123113	3.4	21

240	Room Temperature Single-Electron Narrow-Channel Memory with Silicon Nanodots Embedded in SiO <sub>2</sub> Matrix. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, L792-L795	1.4	21
239	The role of hydrogen radicals in nucleation and growth of nanocrystalline silicon. <i>Journal of Non-Crystalline Solids</i> , <b>1993</b> , 164-166, 993-996	3.9	21
238	Experimental study of self-heating effect (SHE) in SOI MOSFETs: Accurate understanding of temperatures during AC conductance measurement, proposals of 2 $\pi$ method and modified pulsed IV <b>2012</b> ,		20
237	Conducting-tip atomic force microscopy for injection and probing of localized charges in silicon nanocrystals. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3788-3790	3.4	20
236	Blue emission from forward-biased ZnS diodes. <i>Journal of Luminescence</i> , <b>1976</b> , 12-13, 923-927	3.8	20
235	Control of Inter-Dot Electrostatic Coupling by a Side Gate in a Silicon Double Quantum Dot Operating at 4.5 K. <i>Applied Physics Express</i> , <b>2009</b> , 2, 095002	2.4	19
234	In Situ Monitoring of Optical Reflectance Oscillation in Layer-by-Layer Chemical Vapor Deposition of Oxide Superconductor Films. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L1243-L1245	1.4	19
233	High quality a-Si:H films and interfaces prepared by VHF plasma CVD. <i>Journal of Non-Crystalline Solids</i> , <b>1991</b> , 137-138, 677-680	3.9	19
232	Lithographically defined few-electron silicon quantum dots based on a silicon-on-insulator substrate. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 083111	3.4	18
231	An electronic synaptic device based on HfO <sub>2</sub> /TiO <sub>2</sub> bilayer structure memristor with self-compliance and deep-RESET characteristics. <i>Nanotechnology</i> , <b>2018</b> , 29, 415205	3.4	18
230	3-D Design and Analysis of Functional NEMS-gate MOSFETs and SETs. <i>IEEE Nanotechnology Magazine</i> , <b>2007</b> , 6, 218-224	2.6	18
229	Electric Properties of Coplanar High-T <sub>C</sub> Superconducting Field-Effect Devices. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, 492-495	1.4	18
228	Role of Hydrogen Radical Treatment in Nucleation of Nanocrystalline Silicon. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L1443-L1445	1.4	18
227	Electrophotographic studies of glow-discharge amorphous silicon. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , <b>1981</b> , 43, 1079-1089		18
226	Control of Electrostatic Coupling Observed for Silicon Double Quantum Dot Structures. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 4820-4826	1.4	17
225	Integration of Tunnel-Coupled Double Nanocrystalline Silicon Quantum Dots with a Multiple-Gate Single-Electron Transistor. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 4386-4389	1.4	17
224	Preparation of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> Thin Films by Layer-by-Layer Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L787-L789	1.4	17
223	Preparation of Highly Photoconductive a-SiGe <sub>x</sub> from Fluorides by Controlling Reactions with Atomic Hydrogen. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, L540-L543	1.4	17

222	Formation Mechanism of 100-nm-Scale Periodic Structures in Silicon Using Magnetic-Field-Assisted Anodization. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7398-7402	1.4	16
221	Vapor-Liquid-Solid Growth of Small- and Uniform-Diameter Silicon Nanowires at Low Temperature from Si <sub>2</sub> H <sub>6</sub> . <i>Applied Physics Express</i> , <b>2008</b> , 1, 014003	2.4	16
220	Silicon-on-insulator-based radio frequency single-electron transistors operating at temperatures above 4.2 K. <i>Nano Letters</i> , <b>2008</b> , 8, 4648-52	11.5	16
219	Two-Gate Transistor for the Study of Si/SiO <sub>2</sub> Interface in Silicon-on-Insulator Nano-Channel and Nanocrystalline Si Memory Device. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 4637-4641	1.4	16
218	Silicon-based single-electron memory using a multiple-tunnel junction fabricated by electron-beam direct writing. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 1422-1424	3.4	16
217	Preparation of Nanocrystalline Silicon Quantum Dots by Pulsed Plasma Processes with High Deposition Rates. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 571, 43		16
216	Preparation of nanocrystalline silicon quantum dot structure by a digital plasma process. <i>Advances in Colloid and Interface Science</i> , <b>1997</b> , 71-72, 31-47	14.3	15
215	Atomic Layer-by-Layer MOCVD of Complex Metal Oxides and In Situ Process Monitoring. <i>Chemical Vapor Deposition</i> , <b>2001</b> , 7, 7-18		15
214	Ballistic transport in silicon vertical transistors. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 1399-1405	2.5	15
213	Conductance quantization in nanoscale vertical structure silicon field-effect transistors with a wrap gate. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 2922-2924	3.4	15
212	Atomic layer controlled metalorganic chemical vapor deposition of superconducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> films. <i>Journal of Crystal Growth</i> , <b>1994</b> , 145, 232-236	1.6	15
211	Electronic States In Glow-Discharge $\alpha$ -SiGe <sub>x</sub> H:(F) Alloys. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, 49-52	1.4	15
210	High-density assembly of nanocrystalline silicon quantum dots. <i>Current Applied Physics</i> , <b>2006</b> , 6, 344-347	2.6	14
209	Self-aligned double-gate single-electron transistor derived from 0.12- $\mu$ m-scale electron-beam lithography. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2070-2072	3.4	14
208	Electrical Properties of SrTiO <sub>3</sub> /BaTiO <sub>3</sub> Strained Superlattice Films Prepared by Atomic Layer Metallorganic Chemical Vapor Deposition. <i>Journal of the Electrochemical Society</i> , <b>2000</b> , 147, 4615	3.9	14
207	Preparation and Characterization of YBaCuO Superconducting Films by Low-Temperature Chemical Vapor Deposition Using $\beta$ -Diketonate Complex and N <sub>2</sub> O. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, 3839-3843	1.4	14
206	Design of multiple layered $\alpha$ -Si:H(F)/ $\alpha$ -SiGe <sub>x</sub> H:(F) films for enhancement in photoresponse in the near-infrared spectrum. <i>Applied Physics A: Solids and Surfaces</i> , <b>1986</b> , 41, 259-265		14
205	Preparation Method and Optoelectrical Properties of $\alpha$ -Se/Cd <sub>x</sub> Se <sub>1-x</sub> Multilayer Films. <i>Japanese Journal of Applied Physics</i> , <b>1987</b> , 26, 991-995	1.4	14

204	Hole Transport in Silicon Thin Films with Variable Hydrogen Content. <i>Japanese Journal of Applied Physics</i> , <b>1987</b> , 26, L276-L279	1.4	14
203	Characteristics of multilevel storage and switching dynamics in resistive switching cell of Al <sub>2</sub> O <sub>3</sub> /HfO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> sandwich structure. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 025102	3	14
202	Quantum dots in single electron transistors with ultrathin silicon-on-insulator structures. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 013102	3.4	13
201	Dual Function of Single Electron Transistor Coupled with Double Quantum Dot: Gating and Charge Sensing. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CJ01	1.4	13
200	Self-Heating Effects and Analog Performance Optimization of Fin-Type Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CC03	1.4	13
199	Three-Dimensional Numerical Analysis of Switching Properties of High-Speed and Nonvolatile Nanoelectromechanical Memory. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 1132-1139	2.9	13
198	Growth Mechanism of Microcrystalline Silicon Prepared by Alternating Deposition of Amorphous Silicon and Hydrogen Radical Annealing. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L1388-L1391	1.4	13
197	Design of Band Potential with a-SixGe1-x:H(F) Alloys. <i>Japanese Journal of Applied Physics</i> , <b>1987</b> , 26, L169-L172	1.4	13
196	The role of the blocking structure in hydrogenated amorphous silicon vidicon targets. <i>Journal of Applied Physics</i> , <b>1981</b> , 52, 7275-7280	2.5	13
195	Optimized electrical control of a Si/SiGe spin qubit in the presence of an induced frequency shift. <i>Npj Quantum Information</i> , <b>2018</b> , 4,	8.6	13
194	Undoped and catalyst-free germanium nanowires for high-performance p-type enhancement-mode field-effect transistors. <i>Journal of Materials Chemistry C</i> , <b>2016</b> , 4, 5102-5108	7.1	12
193	Atomic layer-by-layer epitaxy of oxide superconductors by MOCVD. <i>Applied Surface Science</i> , <b>1997</b> , 112, 30-37	6.7	12
192	Photoluminescence Study of Self-Limiting Oxidation in Nanocrystalline Silicon Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 664, 2061		12
191	Preparation of Highly Oriented Copper Films by Photo-Assisted Chemical Vapor Deposition Using $\beta$ -Diketonate Complex. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L588-L590	1.4	12
190	Self-limiting adsorption and in situ optical monitoring for atomic layer epitaxy of oxide superconductors layer epitaxy of oxide superconductors. <i>Thin Solid Films</i> , <b>1993</b> , 225, 284-287	2.2	12
189	Designing New Materials with Amorphous Semiconductors -- Structure and Electrical Properties of Multiply Stacked a-Si/a-SiGe <sub>x</sub> Layers --. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, L537-L539	1.4	12
188	Vidicon target of a p-i-n structure using a-Si:H. <i>Journal of Applied Physics</i> , <b>1980</b> , 51, 6422-6423	2.5	12
187	Control of threshold voltage by gate metal electrode in molybdenum disulfide field-effect transistors. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 133507	3.4	11

186	Charge sensing and spin-related transport property of p-channel silicon quantum dots. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 04CK07	1.4	11
185	Germanium nanowires with 3-nm-diameter prepared by low temperature vapour-liquid-solid chemical vapour deposition. <i>Journal of Nanoscience and Nanotechnology</i> , <b>2011</b> , 11, 8163-8	1.3	11
184	Position-Controllable Ge Nanowires Growth on Patterned Au Catalyst Substrate. <i>Applied Physics Express</i> , <b>2009</b> , 2, 015004	2.4	11
183	Carrier transport by field enhanced thermal detrapping in Si nanocrystals thin films. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 124518	2.5	11
182	Electron transport in surface oxidized Si nanocrystal ensembles with thin film transistor structure. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 044511	2.5	11
181	Electron transport through silicon serial triple quantum dots. <i>Solid-State Electronics</i> , <b>2009</b> , 53, 779-785	1.7	11
180	Key capacitive parameters for designing single-electron transistor charge sensors. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 093715	2.5	11
179	Design Optimization of NEMS Switches for Suspended-Gate Single-Electron Transistor Applications. <i>IEEE Nanotechnology Magazine</i> , <b>2009</b> , 8, 174-184	2.6	11
178	Fabrication of Nanocrystalline Si by SiH <sub>4</sub> Plasma Cell. <i>Materials Research Society Symposia Proceedings</i> , <b>1995</b> , 377, 51		11
177	Hole Transport in a-Si:H(F) Prepared by Hydrogen-Radical-Assisted Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, 1783-1787	1.4	11
176	Fabrication of Nanostructure by Anisotropic Wet Etching of Silicon. <i>Japanese Journal of Applied Physics</i> , <b>1988</b> , 27, L1778-L1779	1.4	11
175	Back-action-induced excitation of electrons in a silicon quantum dot with a single-electron transistor charge sensor. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 053119	3.4	10
174	GaAs/AlGaAs field-effect transistor for tunable terahertz detection and spectroscopy with built-in signal modulation. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 122102	3.4	10
173	Demonstration of spin valve effects in silicon nanowires. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 07C508	2.5	10
172	Charge storage and electron/light emission properties of silicon nanocrystals. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2007</b> , 38, 59-63	3	10
171	Influence of the crystal orientation of substrate on low temperature synthesis of silicon nanowires from Si <sub>2</sub> H <sub>6</sub> . <i>Thin Solid Films</i> , <b>2008</b> , 517, 317-319	2.2	10
170	Bottom-up approach to silicon nanoelectronics. <i>Microelectronics Journal</i> , <b>2008</b> , 39, 171-176	1.8	10
169	Superconducting Properties of Ultrathin Films of $\text{YBa}_{2}\text{Cu}_{3}\text{O}_{n}$ Prepared by Metalorganic Chemical Vapor Deposition at $500^{\circ}\text{C}$ . <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, L312-L314	1.4	10



168	. <i>IEEE Transactions on Electron Devices</i> , <b>1988</b> , 35, 919-922	2.9	10
167	Growth of Narrow and Straight Germanium Nanowires by Vapor-Liquid-Solid Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 105002	1.4	10
166	Methodology for Evaluating Operation Temperatures of Fin-Type Field-Effect Transistors Connected by Interconnect Wires. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 064203	1.4	9
165	Experimental Observation of Enhanced Electron-Phonon Interaction in Suspended Si Double Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 045203	1.4	9
164	Field-dependant hopping conduction in silicon nanocrystal films. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 123710	2.5	9
163	In Situ Optical Monitoring of Two-Dimensional Crystal Growth in Layer-by-Layer Chemical Vapor Deposition of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> . <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, L683-L686	1.4	9
162	Electrical properties of a CdTe/InSb hetero metal-insulator-semiconductor structure. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 1306-1307	3.4	9
161	Low-voltage cathodoluminescence of ZnS single crystals. <i>Journal of Luminescence</i> , <b>1978</b> , 16, 323-330	3.8	9
160	Preparation of nanocrystalline silicon quantum dot structure by a digital plasma process. <i>Advances in Colloid and Interface Science</i> , <b>1997</b> , 71-72, 31-47	14.3	9
159	Fabrication and characterization of p-channel Si double quantum dots. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 113110	3.4	8
158	Surface passivation of germanium nanowires using Al <sub>2</sub> O <sub>3</sub> and HfO <sub>2</sub> deposited via atomic layer deposition technique. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 06JG04	1.4	8
157	Scaling Analysis of Nanoelectromechanical Memory Devices. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 044304	1.4	8
156	Experimental evidence of increased deformation potential at MOS interface and its impact on characteristics of ETSOI FETs <b>2011</b> ,		8
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